

Notice of References Cited

Application/Control No.

10/523,636

Applicant(s)/Patent Under
Reexamination
NOTO ET AL.

Examiner

Vicki B. Booker

Art Unit

2813

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,225,648	05-2001	Hsieh et al.	257/95
*	B	US-6,483,127	11-2002	Saeki, Ryo	257/96
	C	US-			
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	I	US-			
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	K	US-			
	L	US-			
	M	US-			

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	N	JP 1992-355541	07-1994	Japan	Toshihiro et al.	
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.